

General Description

The WSD3056DN is the highest performance trench Dual N-Ch MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The WSD3056DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

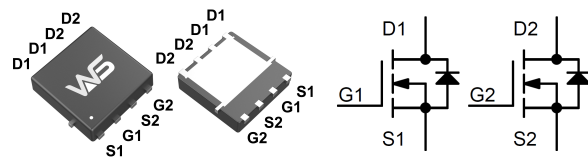
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

B_{VDS}	$R_{DS(on)}$	I_D
30V	13m Ω	35A

Applications

- POL Applications
- MB / VGA / Vcore
- Load Switch
- SMPS 2nd SR

DFN3X3 Dual Pin Configuration

Absolute Maximum Ratings @TA=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current (Continuous) *AC	$T_C=25^\circ C$	35
		$T_C=100^\circ C$	22
I_{DM}	Drain Current (Pulse) *B	140	A
P_D	Power Dissipation	$T_C=25^\circ C$	27
EAS	Single Pulse Avalanche Energy	13	mJ
$R_{\theta JA}$	Thermal Resistance Junction to ambient	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	4.6	$^\circ C/W$
T_I/T_{STG}	Operating Temperature/ Storage Temperature	-55~150	$^\circ C$

Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30 V, V _{GS} = 0V			1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ±20V, V _{DS} = 0V			100	nA
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _{DS} = 250μA	1.2	1.8	2.5	V
R _{DS(on)}	Drain-Source On-state Resistance	V _{GS} = 10V, I _D = 10A		10	13	mΩ
		V _{GS} = 4.5V, I _D = 8A		14	18	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 5V, I _D = 5A		6		S
Switching						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =5A		7.2		nC
Q _{gs}	Gate-Source Charge			2.3		nC
Q _{gd}	Gate-Drain Charge			3		nC
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DD} =15V, I _D =1A, R _G =6Ω		3.8		ns
t _r	Turn-on Rise Time			10		ns
t _{d(off)}	Turn-off Delay Time			22		ns
t _f	Turn-off Fall Time			6.6		ns
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.8		Ω
Dynamic						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		620		pF
C _{oss}	Output Capacitance			85		pF
C _{rss}	Reverse Transfer Capacitance			30		pF
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			35	A
I _{SM}	Pulsed Source Current ³				70	A
V _{SD}	Diode Forward Voltage	I _{SD} = 1A, V _{GS} =0V			1.2	V

Note :

- 1, Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2, V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=16A., R_G=25 , Starting T_J=25°C.
- 3, The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%.
- 4, Essentially independent of operating temperature.

Typical Characteristics

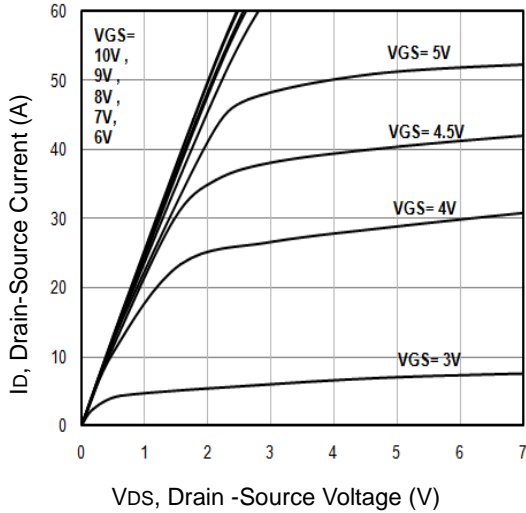


Fig1. Typical Output Characteristics

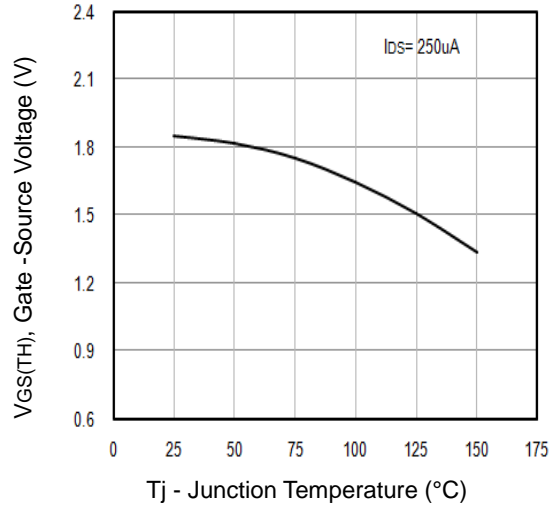


Fig2. Threshold Voltage Vs. Temperature

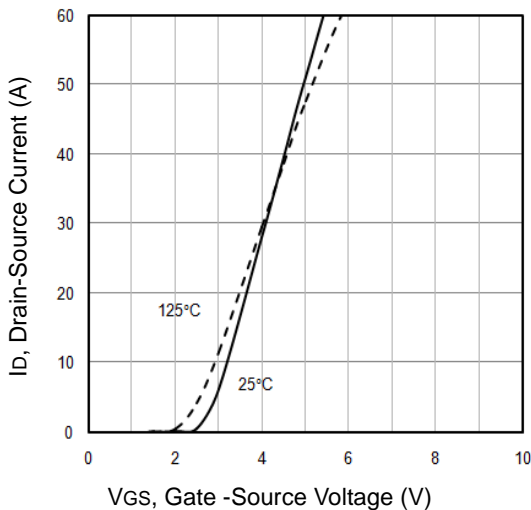


Fig3. Typical Transfer Characteristics

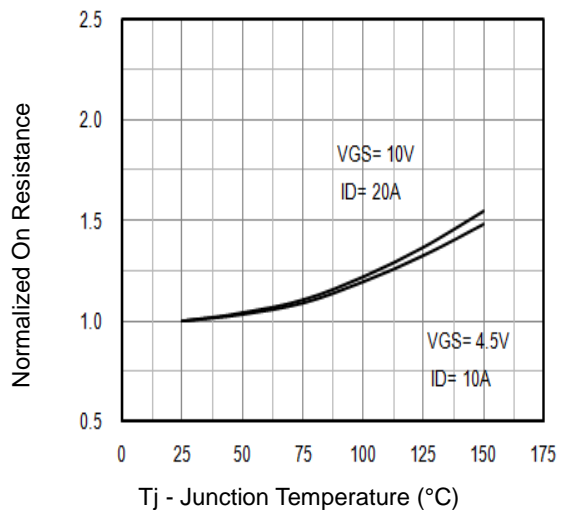


Fig4. Normalized On-Resistance Vs. Temperature

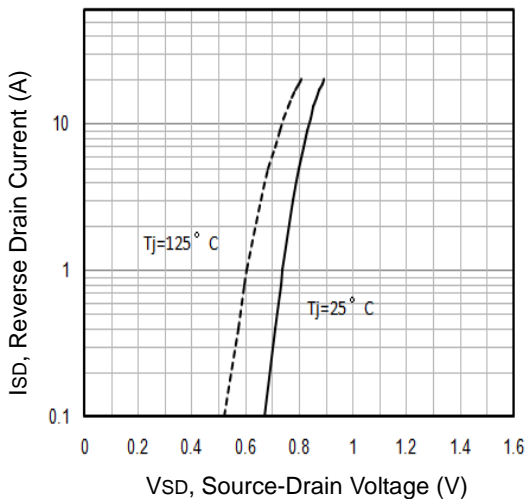


Fig5. Typical Source-Drain Diode Forward Voltage

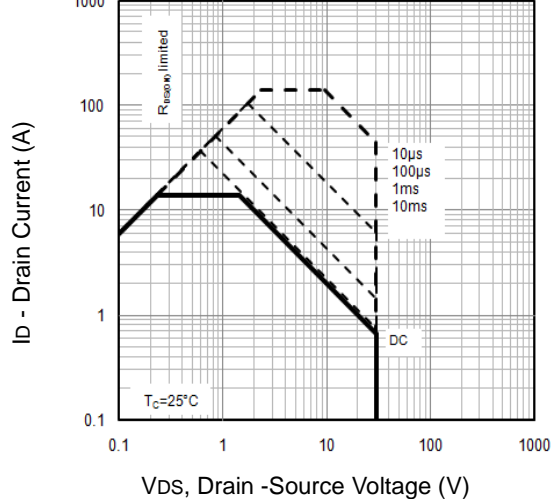


Fig6. Maximum Safe Operating Area

Typical Characteristics

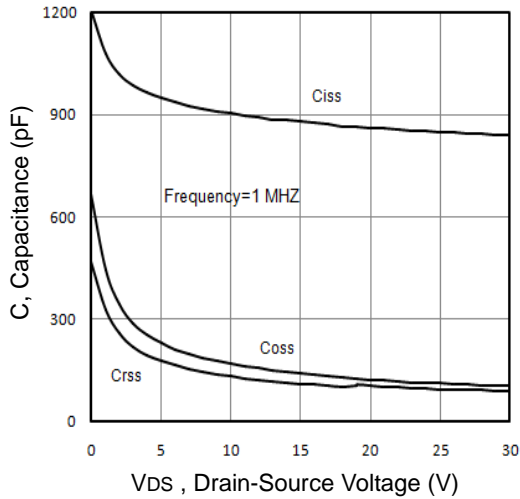


Fig7. Typical Capacitance Vs.Drain-Source Voltage

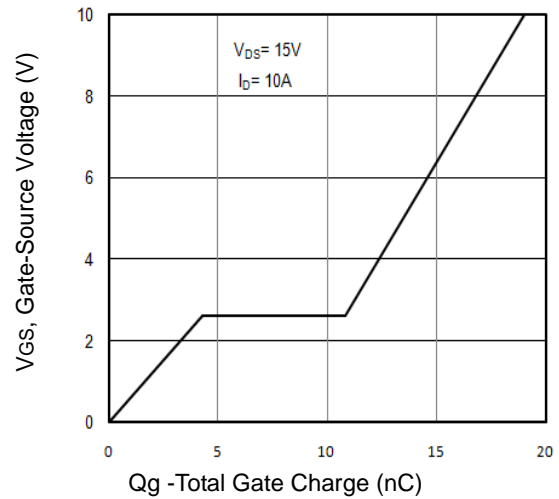


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

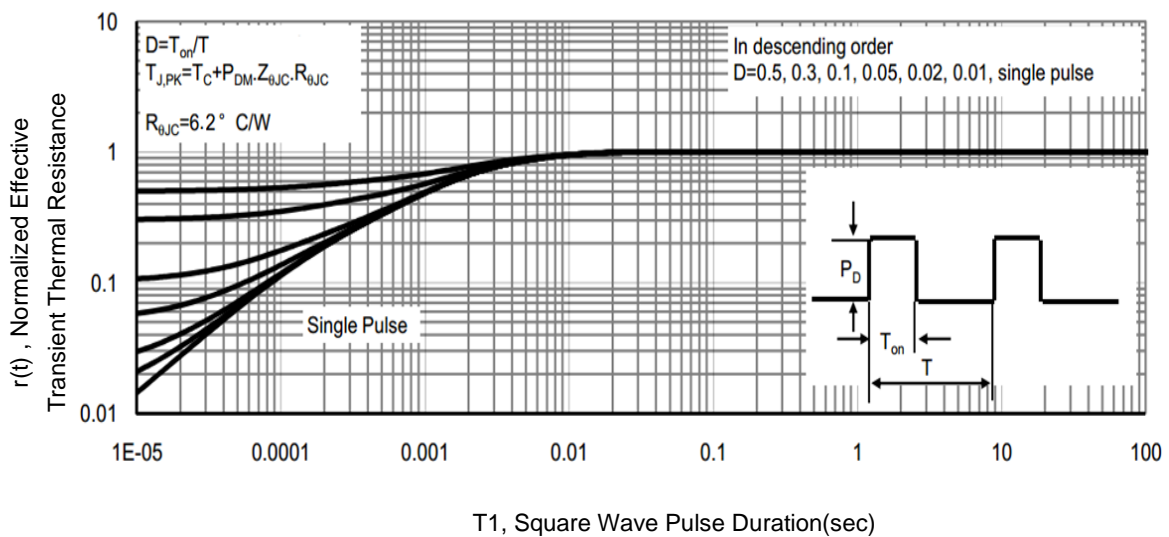


Fig9. T1, Transient Thermal Response Curve

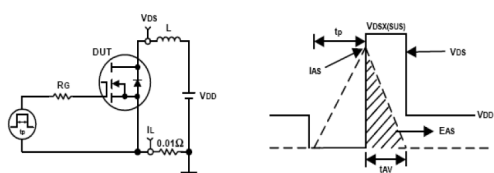


Fig10. Unclamped Inductive Test Circuit and waveforms

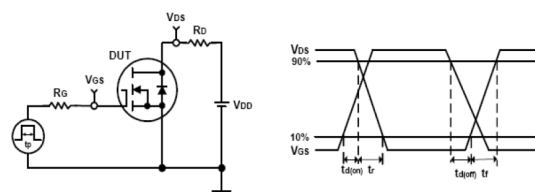


Fig11. Switching Time Test Circuit and waveforms



Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you intend to use.
- 9, this catalog provides information as of Sep. 2014. Specifications and information herein are subject to change without notice.